

Class	Subclass	ISSUE CLASSIFICATION
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JC-535

U.S. UTILITY Patent Application

<p>O.I.P.E.</p> <p>SCANNED <i>IK3</i> O.A. <i>SW</i></p>	<p>PATENT DATE</p>
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APPLICATION NO. 09/858400	CONT/PRIOR D F	CLASS 257-705 438	SUBCLASS 592	ART UNIT 2813 2164	EXAMINER THANH NGUYEN
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APPLICANTS

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TITLE

Process for forming a low resistivity lithium silicide layer on a silicon semiconductor substrate and the resulting device

PTO-2040
12/89[illegible]

<input type="checkbox"/> TERMINAL DISCLAIMER	DRAWINGS			CLAIMS ALLOWED	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	<div>_____ (Assistant Examiner) _____ (Date)</div> <div>_____ (Primary Examiner) _____ (Date)</div> <div>_____ (Legal Instruments Examiner) _____ (Date)</div>			NOTICE OF ALLOWANCE MAILED	
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